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# <u>捷多邦,专业PCB打样工厂,24小时加急出货</u> SN74S225 16 × 5 ASYNCHRONOUS FIRST-IN, FIRST-OUT MEMORY WITH 3-STATE OUTPUTS

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- Independent Asychronous Inputs and Outputs
- 16 Words by 5 Bits
- DC to 10-MHz Data Rate
- 3-State Outputs
- Packaged in Standard Plastic 300-mil DIPs

#### description

This 80-bit active-element memory is a monolithic Schottky-clamped transistor-transistor logic (STTL) array organized as 16 words by 5 bits. A memory system using the SN74S225 easily can be expanded in multiples of 48 words or of 10 bits as shown in Figure 3. The 3-state outputs controlled by a single output-enable ( $\overline{OE}$ ) input make bus connection and multiplexing easy.



A first-in, first-out (FIFO) memory is a storage device that allows data to be written into and read from its array at independent data rates. This FIFO is designed to process data at rates from dc to 10 MHz in a bit-parallel format, word by word.

Reading or writing is done independently, utilizing separate asynchronous data clocks. Data can be written into the array on the low-to-high transition of either load-clock (CLKA, CLKB) input. Data can be read out of the array on the low-to-high transition of the unload-clock (UNCK IN) input (normally high). Writing data into the FIFO can be accomplished in one of two ways:

- In applications not requiring a gated clock control, best results are achieved by applying the clock input to one of the clocks while tying the other clock input high.
- In applications needing a gated clock, the load clock (gate control) must be high for the FIFO to load on the next clock pulse.

CLKA and CLKB can be used interchangeably for either clock gate control or clock input.

Status of the SN74S225 is provided by three outputs. The input-ready (IR) output monitors the status of the last word location and signifies when the memory is full. This output is high whenever the memory is available to accept any data. The unload-clock (UNCK OUT) output also monitors the last word location. This output generates a low-logic-level pulse (synchronized to the internal clock pulse) when the location is vacant. The third status output, output ready (OR), is high when the first word location contains valid data and UNCK IN is high. When UNCK IN goes low, OR will go low and stay low until new valid data is in the first word position. The first word location is defined as the location from which data is provided to the outputs.

The data outputs are noninverted with respect to the data inputs and are 3-state, with a common control input  $(\overline{OE})$ . When  $\overline{OE}$  is low, the data outputs are enabled to function as totem-pole outputs. A high logic level forces each data output to a high-impedance state while all other inputs and outputs remain active. The clear  $(\overline{CLR})$  input invalidates all data stored in the memory array by clearing the control logic and setting OR to a low logic level on the high-to-low transition of a low-active pulse.

The SN74S225 is characterized for operation from 0°C to 70°C.



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# logic symbol<sup>†</sup>



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Standard 91-1984 and IEC Publication 617-12.



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## SN74S225 16 × 5 ASYNCHRONOUS FIRST-IN, FIRST-OUT MEMORY WITH 3-STATE OUTPUTS SDLS207B - SEPTEMBER 1976 - REVISED APRIL 1998

## schematics of inputs and outputs



## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Supply voltage range, V <sub>CC</sub> (see Note 1)	
Input voltage range, V <sub>1</sub>	–0.5 V to 5.5 V
Off-state output voltage range	–0.5 V to 5.5 V
Package thermal impedance, θ <sub>JA</sub> (see Note 2)	
Storage temperature range, T <sub>stg</sub>	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values are with respect to GND.

2. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.



### recommended operating conditions

				NOM	MAX	UNIT	
V <sub>CC</sub> Supply voltage			4.75	5	5.25	V	
VIH High-level input voltage			2			V	
VIL	VIL Low-level input voltage				0.8	V	
ЮН	High-level output current Q c All	Q outputs			-6.5	5 2 mA	
		All other outputs			-3.2		
IOL		Q outputs	16		m۸		
	Low-level output current	All other outputs			8	111/2	
T <sub>A</sub> Operating free-air temperature			0		70	°C	

#### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER			TEST CONDITIONS	MIN	түр†	MAX	UNIT
VIK		V <sub>CC</sub> = 4.75 V,	lj = -18 mA			-1.2	V
VOH	Q outputs	V <sub>CC</sub> = 4.75 V,	I <sub>OL</sub> = -6.5 mA	2.4	2.9		V
	All others	V <sub>CC</sub> = 4.75 V,	$I_{OL} = -3.2 \text{ mA}$	2.4	2.9		
Val	Q outputs	V <sub>CC</sub> = 4.75 V,	I <sub>OL</sub> = 16 mA		0.35	0.5	v
VOL	All others	V <sub>CC</sub> = 4.75 V,	I <sub>OL</sub> = 8 mA		0.35	0.5	
IOZH		V <sub>CC</sub> = 5.25 V,	$V_{O} = 2.4 V$			50	μΑ
I <sub>OZL</sub>		V <sub>CC</sub> = 5.25 V,	$V_{O} = 0.5 V$			-50	μΑ
Ц		V <sub>CC</sub> = 5.25 V,	VI = 5.5 V			1	mA
1	Data		V <sub>I</sub> = 2.7 V			40	
ЧΗ	All others	VCC = 5.25 V,				25	μΑ
1	Data	Voo = 5.25 V	5 V, VI = 0.5 V			-1	٣٨
'IL	All others	VCC = 5.25 V,				-0.25	IIIA
los‡		V <sub>CC</sub> = 5.25 V,	$V_{O} = 0$	-30		-100	mA
ICC§		V <sub>CC</sub> = 5.25 V			80	120	mA

<sup>†</sup> All typical values are at  $V_{CC} = 5 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

<sup>‡</sup> Duration of the short circuit should not exceed one second.

 $\$  I\_CC is measured with all inputs grounded and the outputs open.

### timing requirements over recommended operating conditions (unless otherwise noted) (see Figure 1)

			MIN	NOM	MAX	UNIT
f <sub>clock</sub> Clock frequency					10	MHz
tw		CLKA or CLKB high	25			
	Pulse duration	UNCK IN low	7			ns
		CLR low	40			
t <sub>su</sub>		Data (see Note 3)	-20			ns
	Setup time before CLKAT or CLKBT	CLR inactive	25			
th Hold time after CLKA <sup>↑</sup> or CLKB <sup>↑</sup>		70			ns	

NOTE 3: Data must be set up within 20 ns after the load-clock positive transition.



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switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	түр†	МАХ	UNIT
	CLKA			10	20		MHz
fmax	CLKB		C <sub>L</sub> = 30 pF	10	20		
	UNCK IN			10	20		
tw	UNCK OUT		C <sub>L</sub> = 30 pF	7	14		ns
<sup>t</sup> dis	OE	Any Q	C <sub>L</sub> = 5 pF		10	25	ns
ten	OE	Any Q	C <sub>L</sub> = 30 pF		25	40	ns
<sup>t</sup> PLH		A			50	75	
<sup>t</sup> PHL	UNCK IN	Any Q	CL = 30 pF		50	75	ns
<sup>t</sup> PLH	CLKA or CLKB	OR	C <sub>L</sub> = 30 pF		190	300	ns
<sup>t</sup> PLH		OR	$C_{\rm L} = 30  \rm pE$		40	0 60	ns
<sup>t</sup> PHL	ONOR IN	ÖK	0 <u></u> = 30 pi		30	45	115
	CLR	OR			35	60	
<sup>t</sup> PHL	CLKA or CLKB		C <sub>L</sub> = 30 pF 25 270		25	45	ne
	UNCK IN			400	115		
	CLKA or CLKB	IR			55	75	
	UNCK IN	ID			255	400	
<sup>t</sup> PLH	CLR	IK	C <sub>L</sub> = 30 pF		16	35	ns
	OR↑	Any Q			10	20	

<sup>†</sup> All typical values are at  $V_{CC} = 5 \text{ V}$ ,  $T_A = 25^{\circ}C$ .



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# PARAMETER MEASUREMENT INFORMATION

NOTES: A. CI includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz, Z<sub>0</sub> = 50  $\Omega$ , t<sub>f</sub>  $\leq$  2 ns, t<sub>f</sub>  $\leq$  2

D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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Figure 2. Typical Waveforms for a 16-Word FIFO



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**APPLICATION INFORMATION** 

Figure 3. Word-Width Expansion: 48  $\times$  10 Bits



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